MBR4015CTL

SWITCHMODE™ Power Rectifier

Features and Benefits

- Low Forward Voltage
- Low Power Loss/High Efficiency
- High Surge Capacity
- 150°C Operating Junction Temperature
- 40 A Total (20 A Per Diode Leg)
- Pb−Free Packages are Available*

Applications

- Power Supply – Output Rectification
- Power Management
- Instrumentation

Mechanical Characteristics

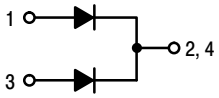
- Case: Epoxy, Molded
- Epoxy Meets UL 94, V−0 @ 0.125 in
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperatures for Soldering Purposes: 260°C Max. for 10 Seconds
- ESD Rating: Human Body Model 3B
  Machine Model C

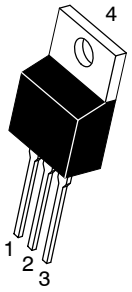
*For additional information on our Pb−Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ON Semiconductor®

http://onsemi.com

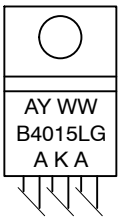
SCHOTTKY BARRIER RECTIFIER 40 AMPERES, 15 VOLTS





TO−220AB
STYLE 6
CASE 221A

MARKING DIAGRAM



A = Assembly Location
Y = Year
WW = Work Week
B4015L = Device Code
G = Pb−Free Package
AKA = Polarity Designator

ORDERING INFORMATION

Device	Package	Shipping
MBR4015CTL	TO−220	50 Units/Rail
MBR4015CTLG	TO−220 (Pb−Free)	50 Units/Rail

Publication Order Number:
MBR4015CTL/D

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V_{RRM} V_{RWM} V_R	15	V
Average Rectified Forward Current (T_C = 140°C per Diode) (T_C = 140°C per Device)	$I_{F(AV)}$	 20 40	A
Peak Repetitive Forward Current, per Diode (Square Wave, 20 kHz, T_C = 135°C)	I_{FRM}	40	A
Non−Repetitive Peak Surge Current (Surge Applied at Rated Load Conditions, Halfwave, Single Phase, 60 Hz)	I_{FSM}	150	A
Peak Repetitive Reverse Surge Current (2.0 μs, 1.0 kHz)	I_{RRM}	1.0	A
Storage Temperature Range	T_{stg}	−65 to +175	°C
Operating Junction Temperature (Note 1)	T_J	−65 to +150	°C
Voltage Rate of Change (Rated V_R)	dv/dt	1,000	V/μs

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. The heat generated must be less than the thermal conductivity from Junction−to−Ambient: $dP_D/dT_J < 1/R_{\theta JA}$.

THERMAL CHARACTERISTICS (Per Diode)

Characteristic	Conditions	Symbol	Max	Unit
Maximum Thermal Resistance, Junction−to−Case	Min. Pad	$R_{\theta JC}$	1.3	°C/W
Maximum Thermal Resistance, Junction−to−Ambient	Min. Pad	$R_{\theta JA}$	70	

ELECTRICAL CHARACTERISTICS

Characteristic	Symbol	Min	Typical	Max	Unit
Instantaneous Forward Voltage (Note 2) (i_F = 20 Amps, T_j = 125°C) (i_F = 40 Amps, Tj = 125°C) (i_F = 20 Amps, Tj = 25°C) (i_F = 40 Amps, Tj = 25°C)	v_F	 − − − −	 0.31 0.45 0.41 0.51	 0.34 0.50 0.43 0.54	V
Instantaneous Reverse Current (Note 2) (Rated dc Voltage, Tj = 125°C) (Rated dc Voltage, Tj = 25°C)	i_R	 − −	 300 0.8	 600 10	mA

2. Pulse Test: Pulse Width = 300 μs, Duty Cycle ≤ 2.0%.

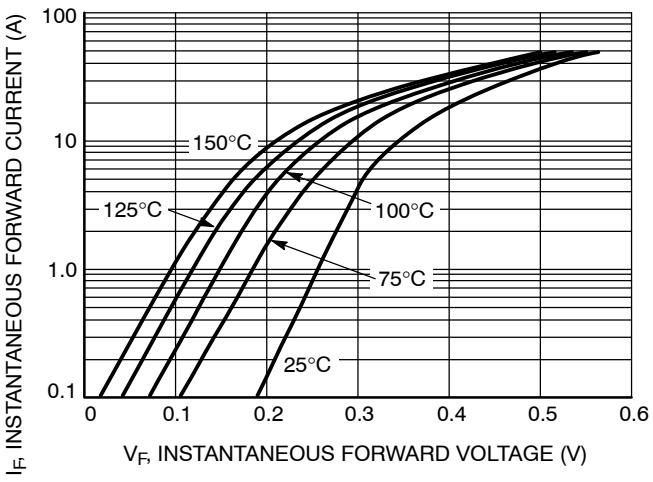


Figure 1. Typical Forward Voltage

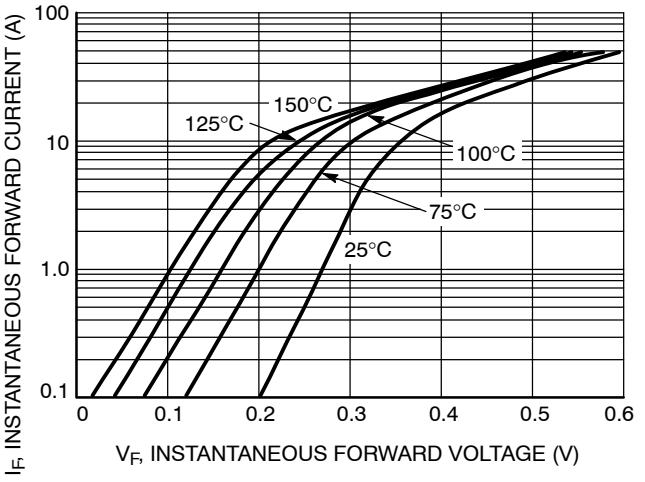


Figure 2. Maximum Forward Voltage

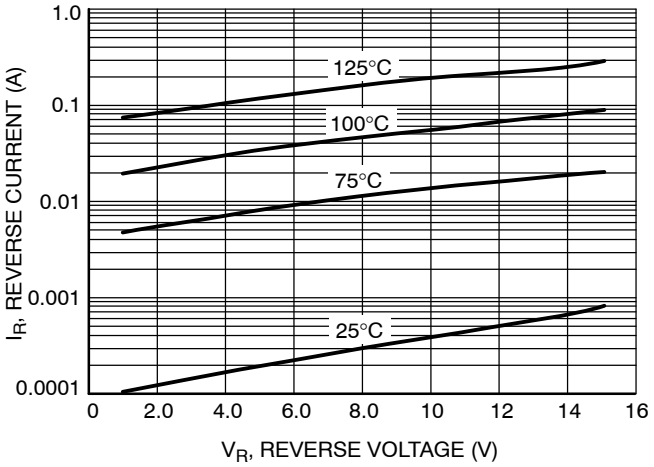


Figure 3. Typical Reverse Current

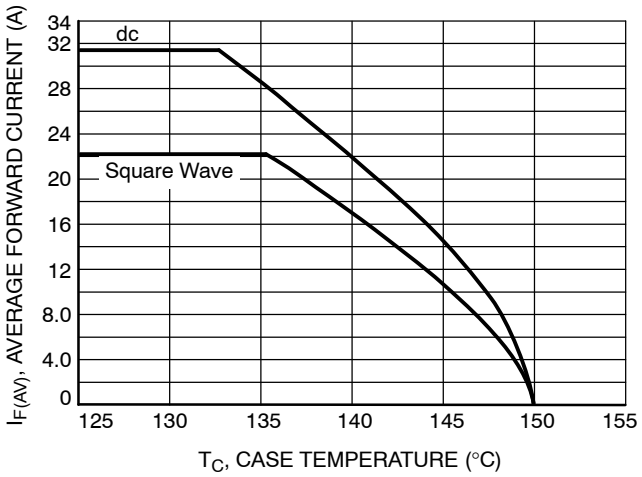


Figure 4. Current Derating, Case, Per Leg

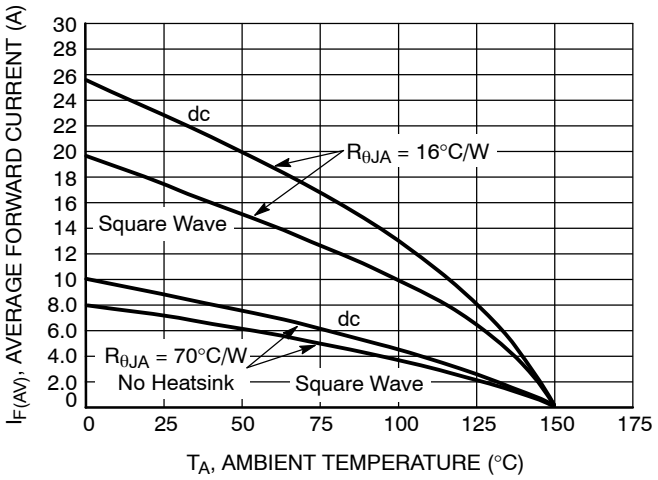


Figure 5. Current Derating, Ambient, Per Leg

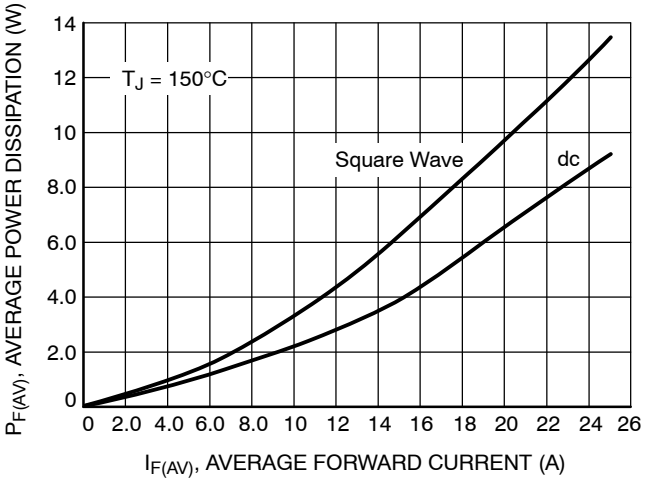


Figure 6. Forward Power Dissipation

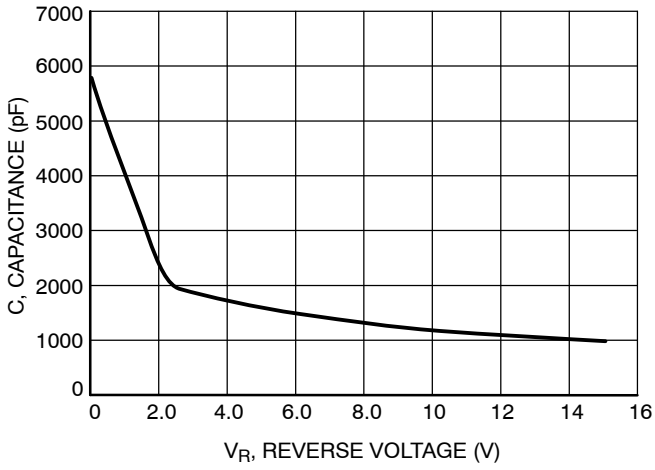
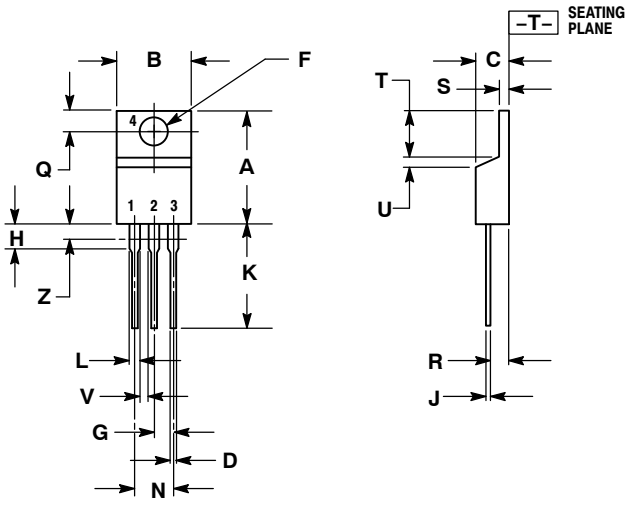


Figure 7. Typical Capacitance

PACKAGE DIMENSIONS

TO−220
CASE 221A−09
ISSUE AF



NOTES:
1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.
3. DIMENSION Z DEFINES A ZONE WHERE ALL BODY AND LEAD IRREGULARITIES ARE ALLOWED.

	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.570	0.620	14.48	15.75
B	0.380	0.405	9.66	10.28
C	0.160	0.190	4.07	4.82
D	0.025	0.035	0.64	0.88
F	0.142	0.161	3.61	4.09
G	0.095	0.105	2.42	2.66
H	0.110	0.155	2.80	3.93
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.15	1.52
N	0.190	0.210	4.83	5.33
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.15	1.39
T	0.235	0.255	5.97	6.47
U	0.000	0.050	0.00	1.27
V	0.045	---	1.15	---
Z	---	0.080	---	2.04

STYLE 6:
PIN 1. ANODE
2. CATHODE
3. ANODE
4. CATHODE

PUBLICATION ORDERING INFORMATION

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